

# isc N-Channel MOSFET Transistor

# MDP1922

**• FEATURES**

- Static drain-source on-resistance:  
 $R_{DS(on)} \leq 8.4m\Omega$
- Enhancement mode
- Fast Switching Speed
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**• APPLICATIONS**

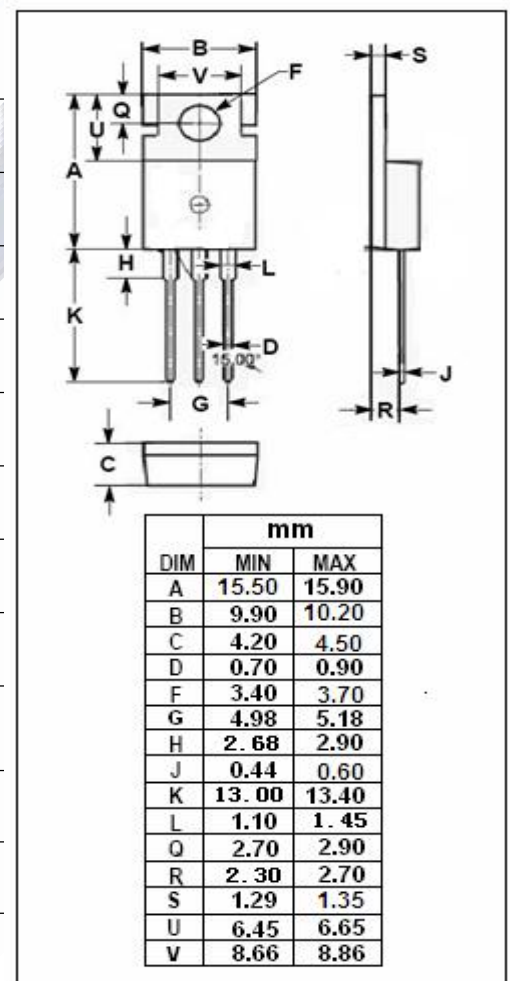
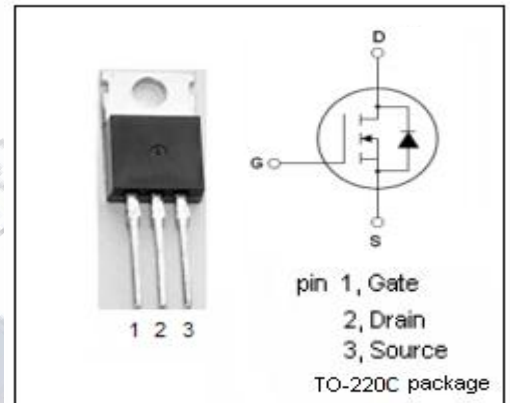
- Be suitable for DC/DC converters and general purpose applications

**• ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ C$ )**

| SYMBOL    | PARAMETER                            | VALUE    | UNIT       |
|-----------|--------------------------------------|----------|------------|
| $V_{DSS}$ | Drain-Source Voltage                 | 100      | V          |
| $V_{GS}$  | Gate-Source Voltage                  | $\pm 20$ | V          |
| $I_D$     | Drain Current-Continuous             | 97       | A          |
| $I_{DM}$  | Drain Current-Single Pulsed          | 384      | A          |
| $P_D$     | Total Dissipation @ $T_c=25^\circ C$ | 157      | W          |
| $T_j$     | Max. Operating Junction Temperature  | 150      | $^\circ C$ |
| $T_{stg}$ | Storage Temperature                  | -55~150  | $^\circ C$ |

**• THERMAL CHARACTERISTICS**

| SYMBOL         | PARAMETER                             | MAX | UNIT         |
|----------------|---------------------------------------|-----|--------------|
| $R_{th(ch-c)}$ | Channel-to-case thermal resistance    | 0.8 | $^\circ C/W$ |
| $R_{th(ch-a)}$ | Channel-to-ambient thermal resistance | 62  | $^\circ C/W$ |



**isc N-Channel MOSFET Transistor**
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**ELECTRICAL CHARACTERISTICS**

 T<sub>C</sub>=25°C unless otherwise specified

| SYMBOL              | PARAMETER                      | CONDITIONS   | MIN | TYP | MAX  | UNIT |
|---------------------|--------------------------------|--|-----|-----|------|------|
| BV <sub>DSS</sub>   | Drain-Source Breakdown Voltage | V <sub>GS</sub> =0V; I <sub>D</sub> =250 μ A               | 100 |     |      | V    |
| V <sub>GS(th)</sub> | Gate Threshold Voltage         | V <sub>DS</sub> =V <sub>GS</sub> ; I <sub>D</sub> =250 μ A | 2   |     | 4    | V    |
| R <sub>DS(on)</sub> | Drain-Source On-Resistance     | V <sub>GS</sub> =10V; I <sub>D</sub> =50A                  |     |     | 8.4  | mΩ   |
| I <sub>GSS</sub>    | Gate-Source Leakage Current    | V <sub>GS</sub> = ±20V; V <sub>DS</sub> =0V                |     |     | ±0.1 | μ A  |
| I <sub>DSS</sub>    | Drain-Source Leakage Current   | V <sub>DS</sub> =80V; V <sub>GS</sub> = 0V                 |     |     | 1    | μ A  |
| V <sub>SD</sub>     | Diode forward voltage          | I <sub>S</sub> =50A; V <sub>GS</sub> = 0V                  |     |     | 1.2  | V    |